

SURFACE MOUNT SILICON ZENER DIODES

BZT52C 4V3S to 39S

SOD-323
 PLASTIC PACKAGE



Marking: As Indicated below with Cathode Band

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT
Maximum Forward Voltage Drop @ $I_F = 10\text{mA}$	V_F	0.9	V
Power Dissipation @ 25°C	* P_D	200	mW
Peak Forward Surge Current, 8.3ms Single Half Sine-Wave Superimposed on Rated Load	** I_{FSM}	2.0	A
Operating Junction and Storage Temperature Range	T_j	- 55 to +150	°C

* Mounted on 5.0mm² (0.13mm thick) land areas

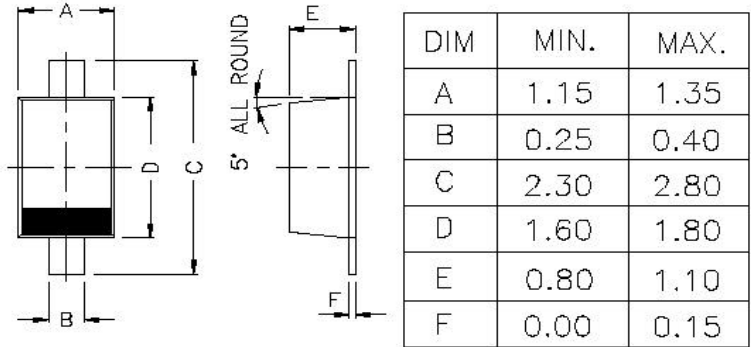
** Measured on 8.3ms, single half sine-wave or equivalent square wave, duty cycle=4 pulses per minute maximum

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$ unless specified otherwise) $V_F @ 10\text{mA} < 0.9\text{V}$

Device #	Zener Voltage		Zener Impedance				Reverse Leakage Current		Marking Code
	$V_Z @ I_{ZT}$		$Z_{ZT} @ I_{ZT}$		$Z_{ZK} @ I_{ZK}$		$I_R @$	V_R	
	(V)		(W)	(mA)	(W)	(mA)	(mA)	(V)	
	min	max	max		max		max		
BZT52C 4V3S	4.09	4.52	95	5.0	500	1.0	5.0	1.0	W7
BZT52C 4V7S	4.47	4.94	78	5.0	500	1.0	5.0	2.0	W8
BZT52C 5V1S	4.85	5.36	60	5.0	480	1.0	0.1	0.8	W9
BZT52C 5V6S	5.32	5.88	40	5.0	400	1.0	0.1	1.0	WA
BZT52C 6V2S	5.89	6.51	10	5.0	200	1.0	0.1	2.0	WB
BZT52C 6V8S	6.46	7.14	8	5.0	150	1.0	0.1	3.0	WC
BZT52C 7V5S	7.13	7.88	7	5.0	50	1.0	0.1	5.0	WD
BZT52C 8V2S	7.79	8.61	7	5.0	50	1.0	0.1	6.0	WE
BZT52C 9V1S	8.65	9.56	10	5.0	50	1.0	0.1	7.0	WF
BZT52C 10S	9.50	10.50	15	5.0	70	1.0	0.1	7.5	WG
BZT52C 11S	10.45	11.55	20	5.0	70	1.0	0.1	8.5	WH
BZT52C 12S	11.40	12.60	20	5.0	90	1.0	0.1	9.0	WI
BZT52C 13S	12.35	13.65	25	5.0	110	1.0	0.1	10	WK
BZT52C 15S	14.25	15.75	30	5.0	110	1.0	0.1	11	WL
BZT52C 16S	15.20	16.80	40	5.0	170	1.0	0.1	12	WM
BZT52C 18S	17.10	18.90	50	5.0	170	1.0	0.1	14	WN
BZT52C 20S	19.00	21.00	50	5.0	220	1.0	0.1	15	WO
BZT52C 22S	20.90	23.10	55	5.0	220	1.0	0.1	17	WP
BZT52C 24S	22.80	25.20	80	5.0	220	1.0	0.1	18	WR
BZT52C 27S	25.65	28.35	80	5.0	250	1.0	0.1	20	WS
BZT52C 30S	28.50	31.50	80	5.0	250	1.0	0.1	22.5	WT
BZT52C 33S	31.35	34.65	80	5.0	250	1.0	0.1	25	WU
BZT52C 36S	34.20	37.80	90	5.0	250	1.0	0.1	27	WW
BZT52C 39S	37.05	40.95	90	5.0	300	1.0	0.1	29	WX

BZT52C4V3S_39S Rev200105E

PACKAGE SOD-323 FL



All dimensions are in mm

CATHODE IS MARKED BY BAND

Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

[查询"BZT52C6V8S"供应商](#)**SOD-323
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Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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